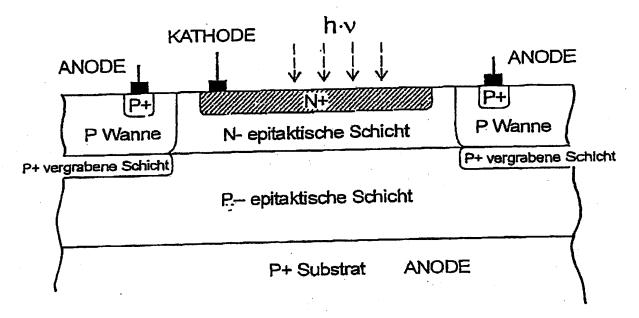
Figure 1



KEY:

ANODE - ANODE

KATHODE - CATHODE

P Wanne - P well

N- epitaktische Schicht - N epitactic layer

P+ vergrabene Schicht - P+ buried layer

P- epitaktische Schicht - P- epitactic layer

P+ Substrat - P+ substrate

Table 1

| | Standard process | | Modified process | |
|----------------------------------|------------------|--------|------------------|--------|
| Optical wavelength λ | 670 nm | 785 nm | 670 nm | 785 nm |
| Quantum efficiency n (%) | 94.3 | 71.3 | 96.5 | 63.4 |
| Sensitivity R (A/W) | 0.508 | 0.450 | 0.520 | 0.400 |
| Rise time t _R (nsec) | 3.00 | 12.40 | 0.610 | 1.465 |
| Fall time t _F (nsec) | 6.50 | 10.40 | 0.515 | 1.480 |
| 3 dB band width NW (MHz) | 79.3 | 30.8 | 625 | 238 |
| Capacity C _D (fF/μm²) | 0.134 | 0.134 | 0.0105 | 0.0105 |

